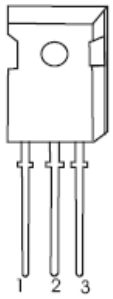
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-247 Plastic-Encapsulate Transistors

TO – 247

1. BASE
2. COLLECTOR
3. EMITTER



2SA1633 TRANSISTOR (PNP)

FEATURES

- High Breakdown Voltage
- High Current and High Power Capability

APPLICATIONS

- For Audio Output Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-10	A
P_C	Collector Power Dissipation	3.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	36	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-50mA,I_B=0	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-120V,I_E=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-10	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-1A	60		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-5A,I_B=-0.5A			-2.5	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-1A	10			MHz